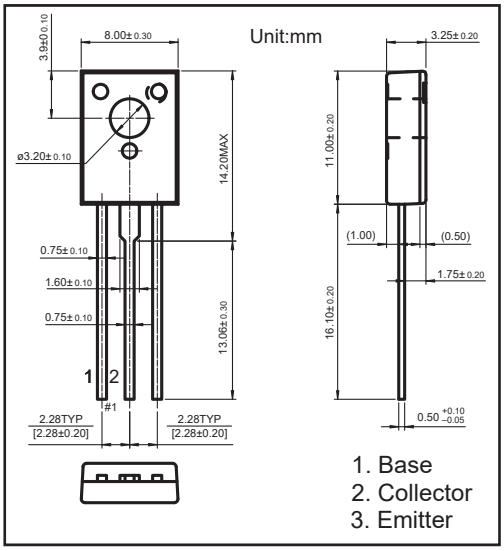
TO-126 Plastic-Encapsulate Transistors

FEATURES

- Low Frequency Power Amplifier
- Collector-Emitter Voltage :-160V
- Current :-1.5A
- PNP Transistor

MECHANICAL DATA

- Case style:TO-126 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector- Base Voltage	V_{CBO}	-180	V
Collector-Emitter Voltage	V_{CEO}	-160	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current -Continuous	I_C	-1.5	A
Collector Dissipation	P_C	1	W
Junction Temperature	T_J	150	℃
Storage Temperature	T_{stg}	-55-150	℃

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	I_C =-1mA,I_E=0	-180			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	I_C=-10mA,I_B=0	-160			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E=-1mA, I_C =0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=-160V,I_E=0			-10	μA
Emitter cut-off current	I_{EBO}	V_{EB}=-4V,I_C=0			-10	μA
DC current gain	$h_{FE(1)}$	V_{CE}=-5V,I_C=-150m A	60		200	
	$h_{FE(2)}$	V_{CE}=-5V,I_C=-500mA	30			
Collector-emitter saturation voltage	$V_{CE(sat)}$	I_C=-500mA,I_B=-50mA			-1	V
Base-emitter voltage	V_{BE}	V_{CE}=-5V,I_C=-150mA			-1.5	V
Transition frequency	f_T	V_{CE}=-5V,I_C=-150mA		140		MHz
Collector output capacitance	C_{ob}	V_{CB}=-10V,I_E=0,f=1MHz		27		pF